
2SC5051

Silicon NPN Epitaxial

HITACHI

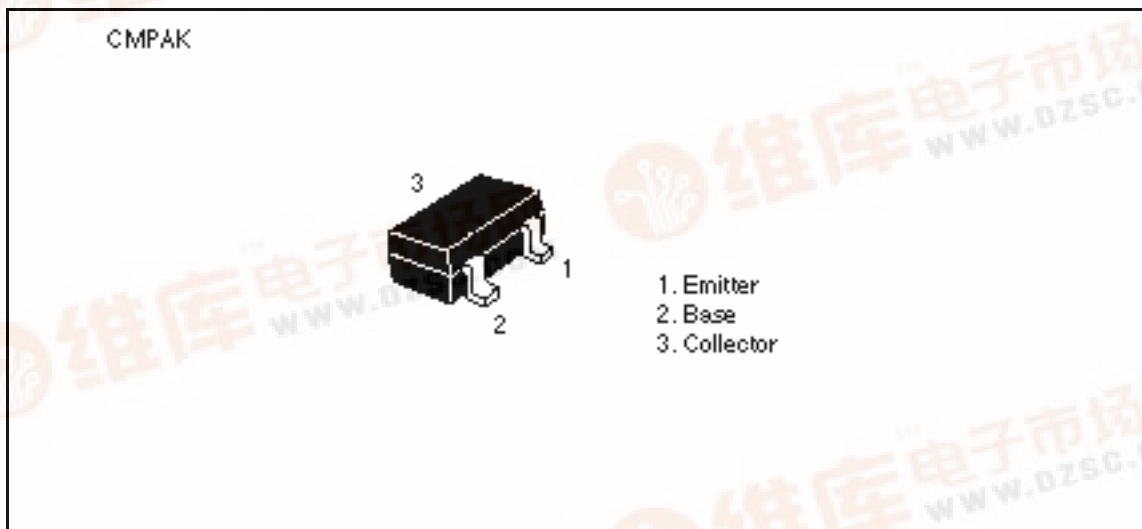
Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 11 \text{ GHz Typ}$
- High gain, low noise figure
 $PG = 14.5 \text{ dB Typ, NF} = 1.1 \text{ dB Typ at } f = 900 \text{ MHz}$

Outline



2SC5051

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

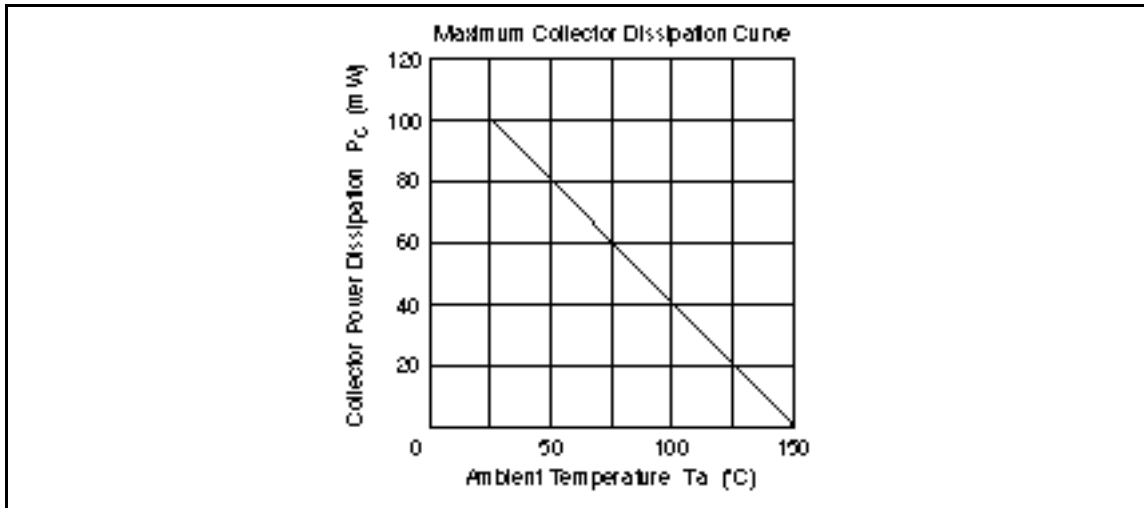
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 12 V, I_E = 0$
	I_{CEO}	—	—	1	mA	$V_{CE} = 8 V, R_{BE} =$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	C_{ob}	—	0.65	1.15	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	8.0	11.0	—	GHz	$V_{CE} = 5 V, I_C = 20 mA$
S21 Parameter	$ S_{21} $	—	14.0	—	dB	$V_{CE} = 5 V, I_C = 20 mA,$ $f = 1000 MHz$
Power gain	PG	11.5	14.5	—	dB	$V_{CE} = 5 V, I_C = 20 mA,$ $f = 900 MHz$
Noise figure	NF	—	1.1	2.0	dB	$V_{CE} = 5 V, I_C = 5 mA,$ $f = 900 MHz$

Note: Marking is "YZ-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

See characteristic curves of 2SC4926.



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Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan
Tel Tokyo (03) 3270-2111
Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-4835
U.S.A.
Tel 415-589-8300
Fax 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher StraÙe 3
D-85622 Feldkirchen
München
Tel 089-9 94 80 0
Fax 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitbrook Park
Lower Cookham Road
M Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel 0628-885000
Fax 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel 535-2100
Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel 27359218
Fax 27308074